

# **TSM05N03**

# 30V N-Channel MOSFET



**SOT-223** 

#### Pin Definition:

- 1. Gate
- 2. Drain
- 3. Source

#### **PRODUCT SUMMARY**

V <sub>DS</sub> (V)	$R_{DS(on)}(m\Omega)$	I <sub>D</sub> (A)
30	60 @ V <sub>GS</sub> =10V	5
	90 @ V <sub>GS</sub> =4.5V	3.8

#### **Features**

- Advance Trench Process Technology
- High Density Cell Design for Ultra Low On-resistance

## **Application**

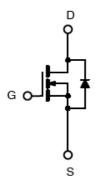
- Load Switch
- PA Switch

#### **Ordering Information**

Part No.	Package	Packing		
TSM05N03CW RPG	SOT-223	2.5Kpcs / 13" Reel		

Note: "G" denotes Halogen Free Product.

### **Block Diagram**



N-Channel MOSFET

#### **Absolute Maximum Rating** (Ta = 25°C unless otherwise noted)

Parameter	Symbol	Limit	Unit		
Drain-Source Voltage		$V_{DS}$	30	V	
Gate-Source Voltage		$V_{GS}$	±20	V	
Continuous Drain Current	Continuous Drain Current		5	А	
Pulsed Drain Current		I <sub>DM</sub>	±20	А	
Continuous Source Current (Diode Condu	Continuous Source Current (Diode Conduction) <sup>a,b</sup>		1.7	А	
Martin as Borras Biratington	Ta = 25°C	P <sub>D</sub>	3	W	
Maximum Power Dissipation	Ta = 75°C		1.1		
Operating Junction Temperature		TJ	+150	°C	
Operating Junction and Storage Temperature Range		T <sub>J</sub> , T <sub>STG</sub>	-55 to +150	°C	

#### **Thermal Performance**

Parameter	Symbol	Limit	Unit
Junction to Case Thermal Resistance	R⊖ <sub>JC</sub>	15	°C/W
Junction to Ambient Thermal Resistance (PCB mounted)	$R\Theta_{JA}$	45	°C/W

- a. Pulse width limited by the Maximum junction temperature
- b. Surface Mounted on a 1 in<sup>2</sup> pad of 2oz Cu,  $t \le 5$  sec.

1/4 Version: A12



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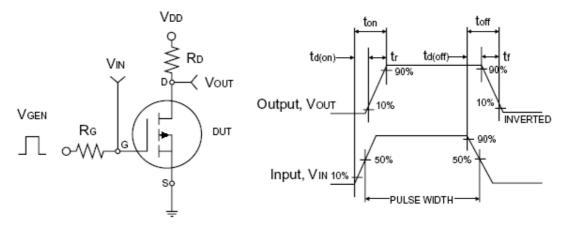


**Electrical Specifications** (Ta = 25°C unless otherwise noted)

Parameter	Conditions	Symbol	Min	Тур	Max	Unit
Static						
Drain-Source Breakdown Voltage	$V_{GS} = 0V, I_D = 250\mu A$	BV <sub>DSS</sub>	30			V
Gate Threshold Voltage	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	$V_{GS(TH)}$	1		3	V
Gate Body Leakage	$V_{GS} = \pm 20V, V_{DS} = 0V$	I <sub>GSS</sub>			±100	nA
Zero Gate Voltage Drain Current	$V_{DS} = 30V, V_{GS} = 0V$	I <sub>DSS</sub>			1.0	μA
On-State Drain Current	$V_{DS} = 5V, V_{GS} = 10V$	I <sub>D(ON)</sub>	5			Α
Drain-Source On-State Resistance	$V_{GS} = 10V, I_D = 5A$			46	60	mΩ
Drain-Source On-State Resistance	$V_{GS} = 4.5V, I_D = 3.8A$	R <sub>DS(ON)</sub>	1	70	90	
Forward Transconductance	$V_{DS} = 10V, I_{D} = 5A$	g <sub>fs</sub>	1	5		S
Diode Forward Voltage	$I_S = 2.5A, V_{GS} = 0V$	$V_{SD}$	1		1.2	V
Dynamic <sup>b</sup>						
Total Gate Charge	\/ 40\/ L 5A	$Q_g$		4.2	7	
Gate-Source Charge	$V_{DS} = 10V, I_D = 5A,$ $V_{GS} = 5V$	$Q_{gs}$		1.9		nC
Gate-Drain Charge	v <sub>GS</sub> = 3 v	$Q_{gd}$		1.35		
Input Capacitance	$V_{DS} = 15V, V_{GS} = 0V,$ f = 1.0MHz	C <sub>iss</sub>		555		
Output Capacitance		C <sub>oss</sub>		120		pF
Reverse Transfer Capacitance	1 = 1.0IVIM2	C <sub>rss</sub>		60		
Switching <sup>b.c</sup>						
Turn-On Delay Time	\/ 40\/ D 450	t <sub>d(on)</sub>		4.2	5.5	
Turn-On Rise Time	$V_{DD} = 10V, R_L = 15\Omega,$ $I_D = 1A, V_{GEN} = 10V,$	t <sub>r</sub>		19	25	20
Turn-Off Delay Time		t <sub>d(off)</sub>		13	17	nS
Turn-Off Fall Time	$R_G = 6\Omega$	t <sub>f</sub>		9	12	

#### Notes:

- a. pulse test: PW ≤300µS, duty cycle ≤2%
- b. For DESIGN AID ONLY, not subject to production testing.
- c. Switching time is essentially independent of operating temperature.



**Switching Test Circuit** 

Switchin Waveforms

2/4 Version: A12

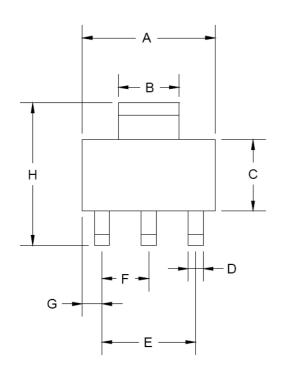


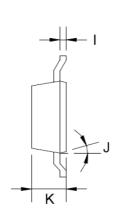
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# **SOT-223 Mechanical Drawing**





SOT-223 DIMENSION					
DIM	MILLIMETERS		INCHES		
	MIN	MAX	MIN	MAX	
Α	6.350	6.850	0.250	0.270	
В	2.900	3.100	0.114	0.122	
С	3.450	3.750	0.136	0.148	
D	0.595	0.635	0.023	0.025	
Е	4.550	4.650	0.179	0.183	
F	2.250	2.350	0.088	0.093	
G	0.835	1.035	0.032	0.041	
Н	6.700	7.300	0.263	0.287	
I	0.250	0.355	0.010	0.014	
J	10°	16°	10°	16°	
K	1.550	1.800	0.061	0.071	



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